

PMF370XN

N-channel TrenchMOS extremely low level FET

Product data sheet

1. General description

Extremely low level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- · Low threshold voltage
- Saves PCB space due to small footprint (40 % smaller than SOT23)
- · Suitable for low gate drive sources
- · Surface-mounted package

3. Applications

- · Driver circuits
- Switching in portable appliances

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	-	30	V
I _D	drain current	V _{GS} = 4.5 V; T _{sp} = 25 °C	-	-	0.87	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	-	0.56	W
Static characte	eristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 \text{ °C}$	-	370	440	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	□ 3	D
2	S	source		
3	D	drain		G—(F)
				mbb076 S
			1 2	
			SC-70 (SOT323)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF370XN	SC-70	plastic surface-mounted package; 3 leads	SOT323			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMF370XN	F6%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{sp} = 25 °C	-	0.87	Α
		V _{GS} = 4.5 V; T _{sp} = 100 °C	-	0.55	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$	-	1.74	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	0.56	W
T _j	junction temperature		-55	150	°C
T _{stg}	storage temperature		-55	150	°C
I _S	source current	T _{sp} = 25 °C	-	0.47	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{sp} = 25 ^{\circ}C$	-	0.94	Α

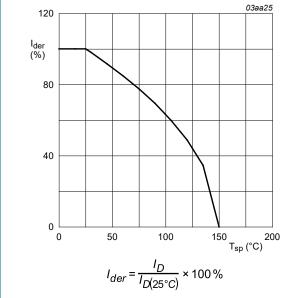


Fig. 1. Normalized continuous drain current as a function of solder point temperature

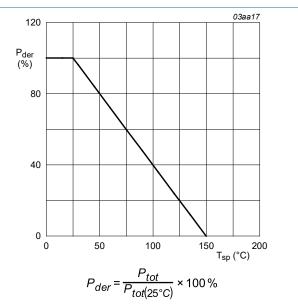
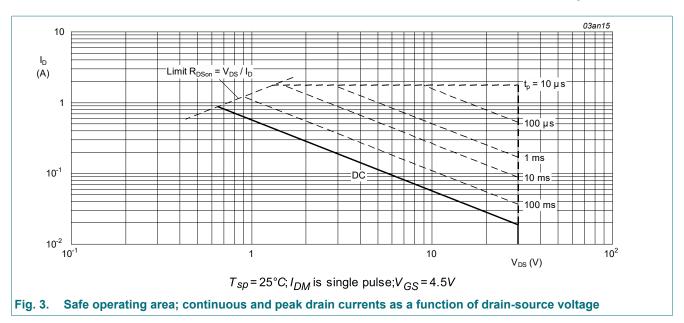


Fig. 2. Normalized total power dissipation as a function of solder point temperature

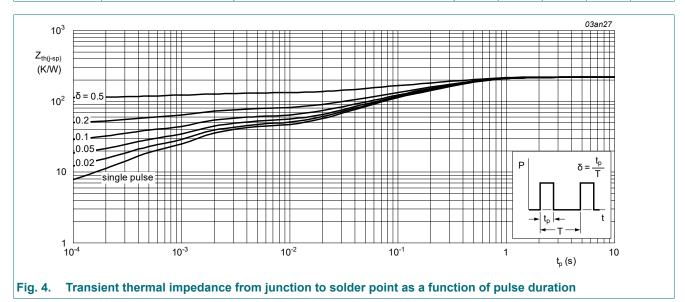


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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from		-	-	220	K/W
	junction to solder point					



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = -55 ^{\circ}C$	-	-	1.8	V
	voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 150 °C	0.35	-	-	V
		I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C	0.5	1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 70 °C	-	-	2	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 2.5 \text{ V}; I_D = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	550	650	mΩ
resistance		V _{GS} = 4.5 V; I _D = 0.2 A; T _j = 150 °C	-	629	748	mΩ
	V _{GS} = 4.5 V; I _D = 0.2 A; T _j = 25 °C	-	370	440	mΩ	
Dynamic ch	aracteristics		'		'	
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 1 A; V _{GS} = 4.5 V;	-	0.65	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.14	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; f = 1 MHz; V _{GS} = 0 V;	-	37	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	8.5	-	pF
C _{rss}	reverse transfer capacitance		-	5.5	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 15 Ω ; V_{GS} = 4.5 V;	-	6.5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	9.5	-	ns
t _{d(off)}	turn-off delay time]	-	14	-	ns
t _f	fall time	1	-	5.5	-	ns
Source-drai	in diode		1			
V _{SD}	source-drain voltage	I _S = 0.3 A; V _{GS} = 0 V; T _i = 25 °C	-	0.81	1.2	V

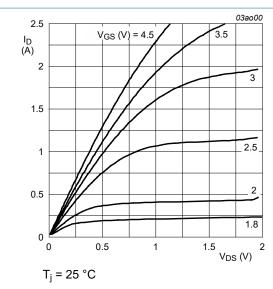


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

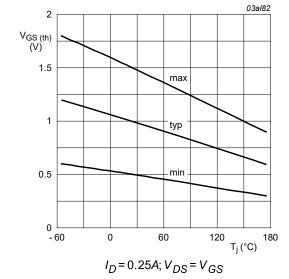


Fig. 7. Gate-source threshold voltage as a function of junction temperature

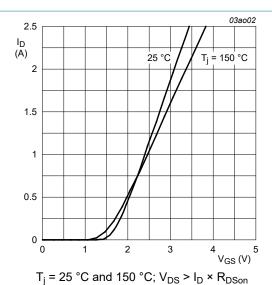


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

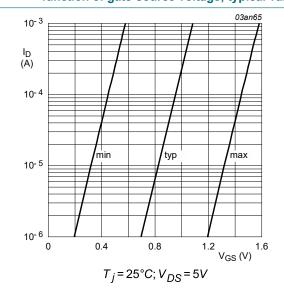


Fig. 8. Subthreshold drain current as a function of gate-source voltage

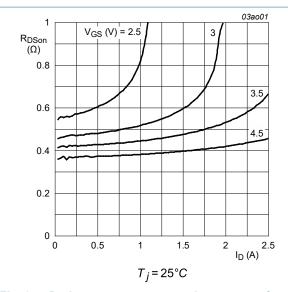


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

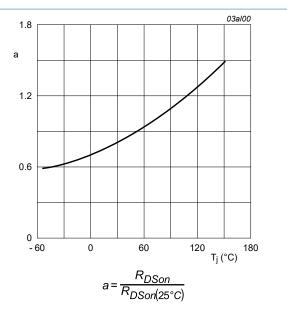


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

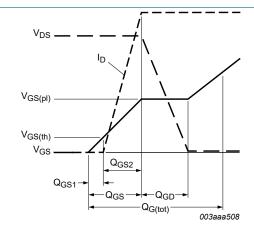


Fig. 11. Gate charge waveform definitions

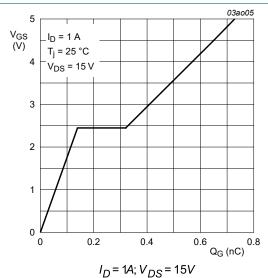


Fig. 12. Gate-source voltage as a function of gate charge; typical values

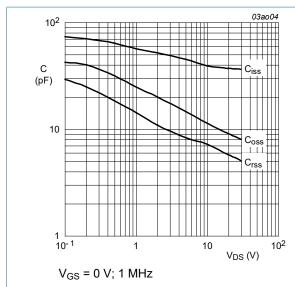
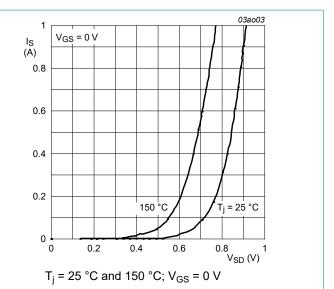


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source current as a function of source-drain as a function of drain-source voltage; typical values



voltage; typical values

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11. Package outline

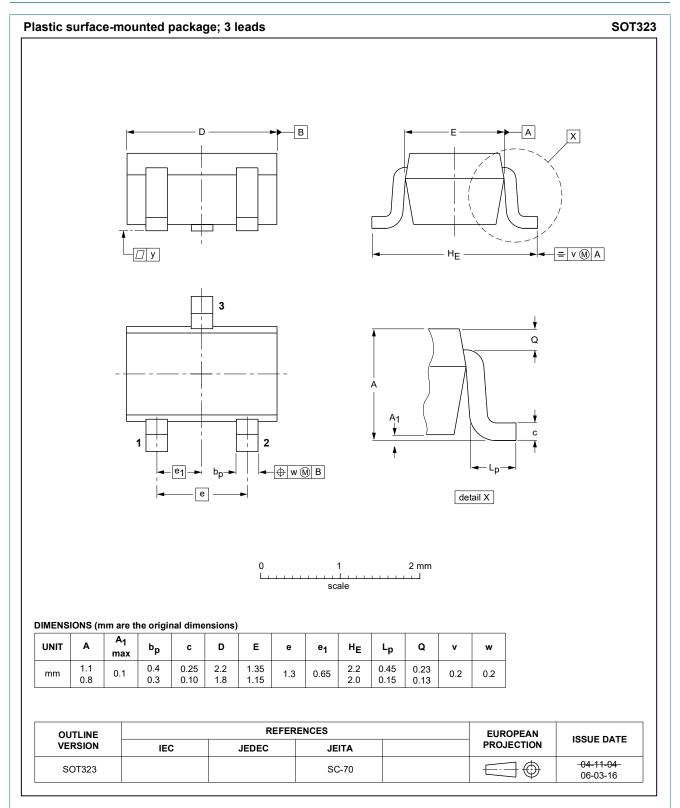
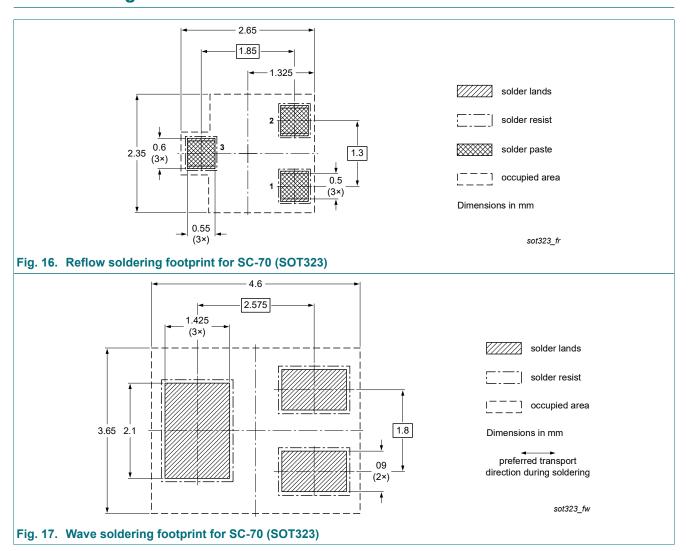


Fig. 15. Package outline SC-70 (SOT323)

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12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	B.4 I		
	rtolougo duto	Data sheet status	Change notice	Supersedes
PMF370XN v.4	20190705	Product data sheet	-	PMF370XN v.3
Modifications:	 Legal texts hav 	conditions for V _{(BR)DSS} revise e been adapted to the new c nis data sheet has been rede	ompany name where a	• • •
PMF370XN v.3	20080620	Product data sheet	-	PMF370XN v.2
PMF370XN v.2	20051206	Product data sheet	-	PMF370XN v.1
PMF370XN v.1	20040211	Product data sheet	-	-

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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